



TO-252-2L Plastic-Encapsulate MOSFETS

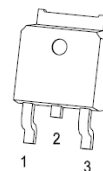
CJU40P04 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-40V	14mΩ@-10V	-40A

DESCRIPTION

The CJU40P04 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for high current load applications.

TO-252-2L



1. GATE
2. DRAIN
3. SOURCE

FEATURES

- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

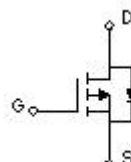
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING



CJU40P04= Device code
Solid dot = Green molding compound device,
if none, the normal device
XXX=Date Code

EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-40	A
Pulsed Drain Current	I_{DM}	-160	A
Single Pulsed Avalanche Energy	$E_{AS}^{(1)}$	544	mJ
Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	$^{\circ}\text{C}$

(1). E_{AS} condition: $V_{DD}=-20\text{V}$, $L=1\text{mH}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

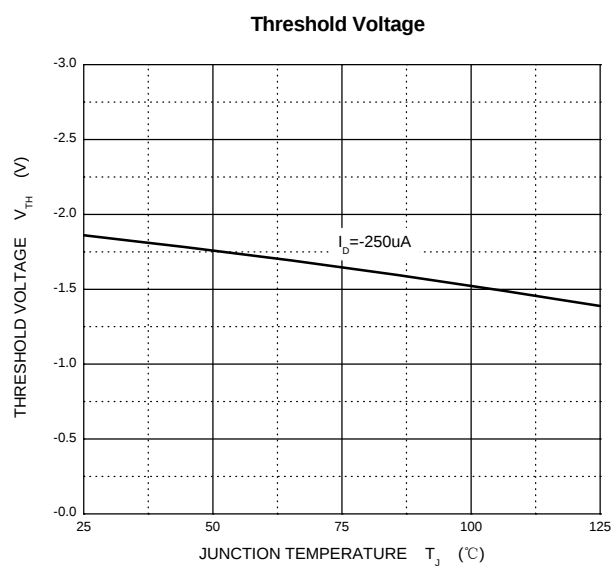
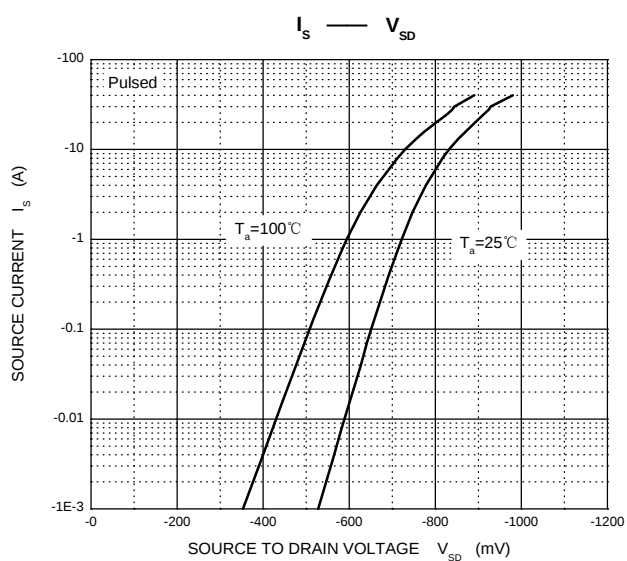
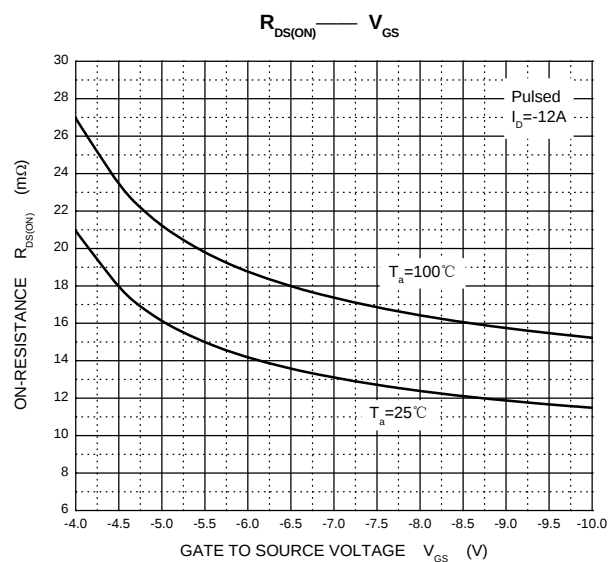
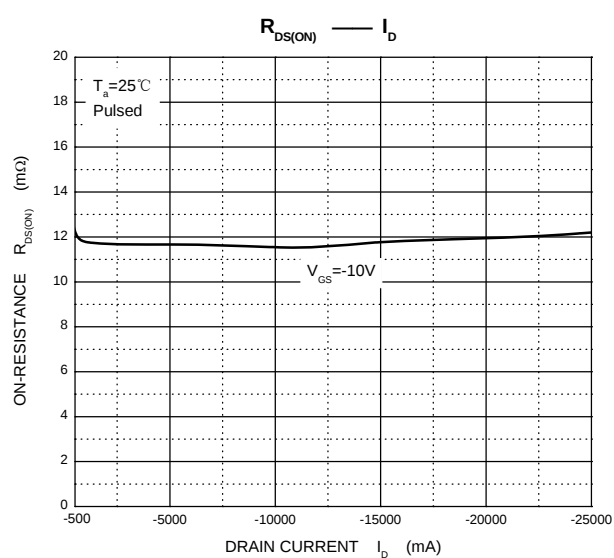
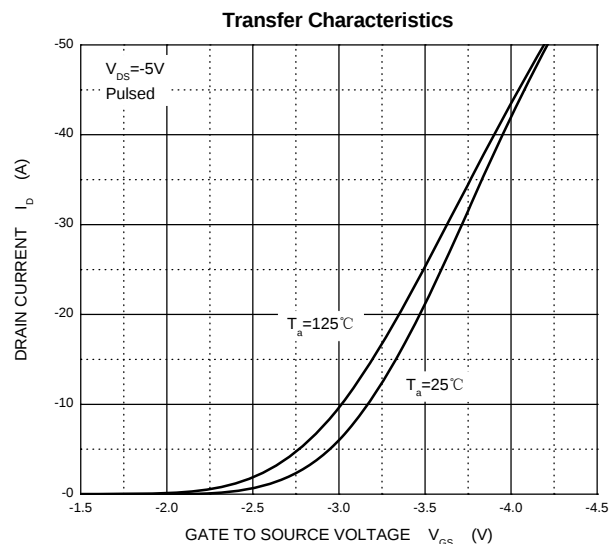
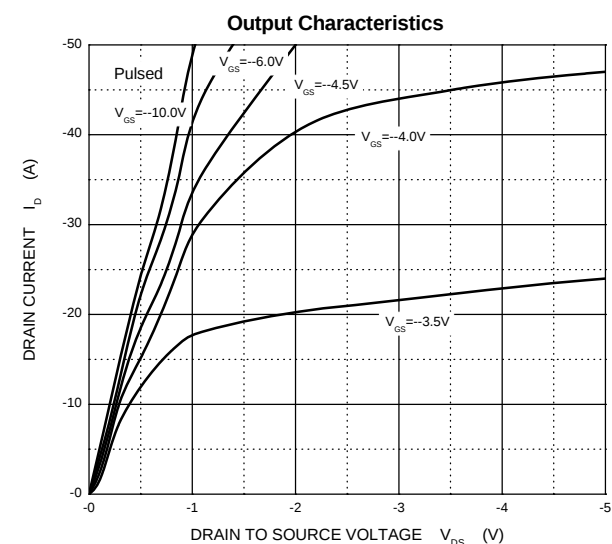
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR) DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -40V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
On characteristics (note1)						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.5	-1.85	-3	V
Static drain-source on-sate resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -12A$		12	14	m Ω
Forward transconductance	g_{FS}	$V_{DS} = -5V, I_D = -12A$	34			S
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = -20V, V_{GS} = 0V,$ $f = 1MHz$		2960		pF
Output capacitance	C_{oss}			370		
Reverse transfer capacitance	C_{rss}			310		
Switching characteristics (note 2)						
Total gate charge	Q_g	$V_{DS} = -20V, V_{GS} = -10V,$ $I_D = -12A$		72		nC
Gate-source charge	Q_{gs}			14		
Gate-drain charge	Q_{gd}			15		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -20V, I_D = -20A$ $V_{GS} = -10V, R_G = 3\Omega,$		10		ns
Turn-on rise time	t_r			18		
Turn-off delay time	$t_{d(off)}$			38		
Turn-off fall time	t_f			24		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V_{SD}	$V_{GS} = 0V, I_S = -20A$			-1.2	V
Continuous drain-source diode forward current (note3)	I_S				-40	A
Pulsed drain-source diode forward current	I_{SM}				-160	A

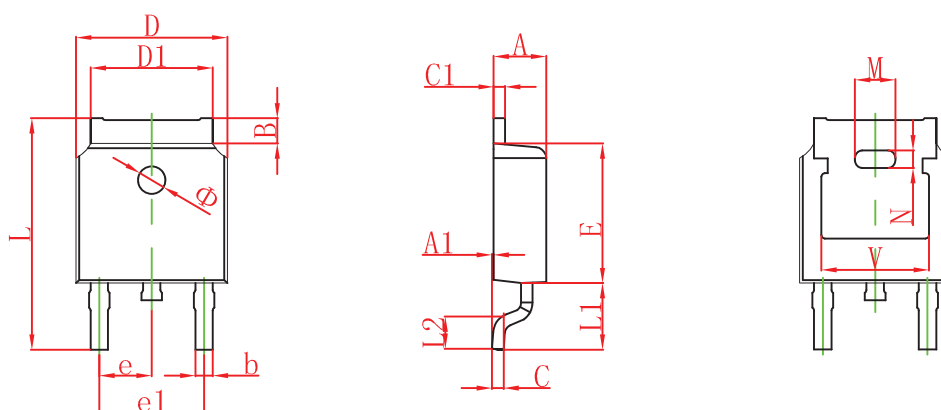
Notes:

1. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production.
3. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Typical Characteristics

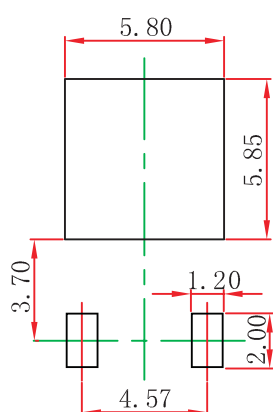


TO-252(4R)-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

TO-252(4R)-2L Suggested Pad Layout



Note:

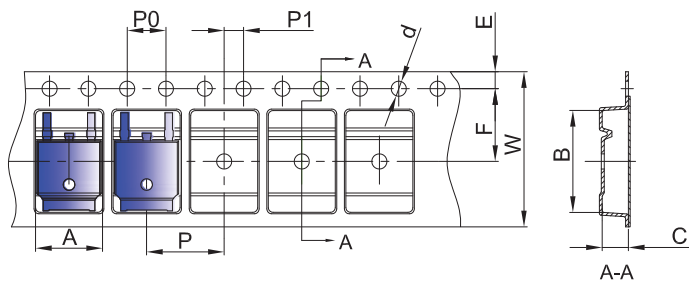
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

To-252(4R)-2L Tape and Reel

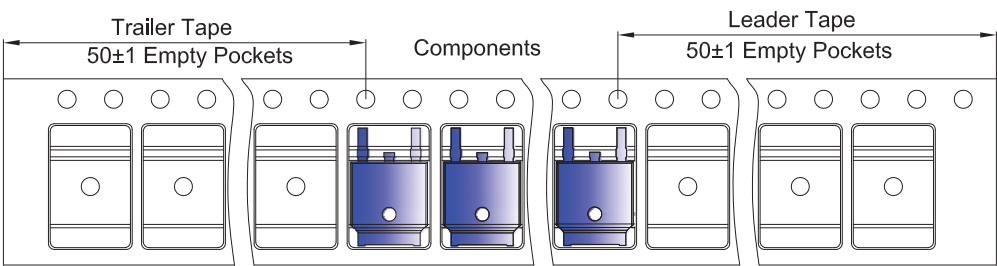
TO-252 Embossed Carrier Tape



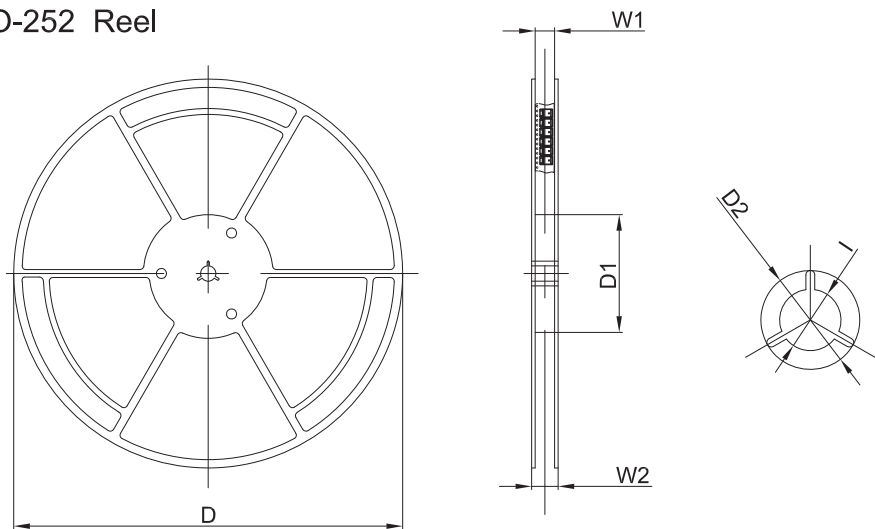
Packaging Description:
 TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	